Appl. No. : **10/606,001**
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AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0015] on Page 6 which begins with "Figure 4B" with the following paragraph:

[0015] FIG. 4B shows a block diagram of a precursor stack 400B designed for use in the fabrication of an interferometric modulator device. The stack 400B includes a conductor stack 404, the composition of which has been described above. Suitable metals for the conductor stack 404 in the present case include glossy metals such as Chromium, Tungsten, Molybdenum, or alloys thereof. The conductor stack 404 may have a thickness of up to 150 angstroms. Transparent conductors suitable for use in the conductor stack 404 include indium tin oxide (ITO), zinc oxide (ZnO), and titanium nitride (TiN). Typical thicknesses for the transparent conductors range from 100 to 800 angstroms. The conductor stack 404 resides on a transparent compensating oxide layer 410, in one embodiment. An optical compensation layer may comprise the oxide layer 410, which may be of a metallic oxide, such as zirconia (ZrO2) or hafnia (HfO2), which have a finite extinction coefficient within the visible range. The compensating oxide layer 410 is an optional film for all the designs discussed in this patent application. Typical thicknesses for the oxide layer 410 range from 100 to 800 angstroms. It should be noted that the positions of the conductor stack 404 and the compensating oxide layer 410 are interchangeable with only subtle changes in the optical behavior. This design, however, can be considered an embedded optical film design since the metal, which plays the primary optical function, resides on the side of insulator layer 406, opposite that of the sacrificial layer 408. The insulator layer 406, may comprise a silicon dioxide film with a thickness ranging from 280 to 840 angstroms for good black states, although other thicknesses are useful for different interference modulator operational modes. Other oxides or combinations of oxides are possible as well. In another embodiment, the optical compensation layer may comprise a material such as a nitride or a fluoride. The sacrificial layer 408 may include a single layer of materials such as silicon, molybdenum, tungsten, for example, which are all etchable by XeF2, a process etch gas which has been described in prior patents. For the stack 400B, the thickness of the layer 408 may vary from 1000, to 7000 angstroms.